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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Complete If Known

Application Number	09/747,779
Filing Date	December 22, 2000
First Named Inventor	Kim, Hong Koo
Group Art Unit	1765
Examiner Name	Unassigned

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Attorney Docket Number

000939-073311US

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS		
Examiner Initials *	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
	AA	BASIT et al., "Growth of highly oriented Pb(Zr, Ti)O ₃ films on MgO-buffered oxidized Si substrates and its application to ferroelectric nonvolatile memory field-effect transistors," <u>Applied Physics Letters</u> , 73(26):3941-3943 (1998).
	AB	BASIT et al., "Temperature dependence of lead loss in r.f. magnetron sputtering of a stoichiometric Pb(Zr, Ti)O ₃ target," <u>Thin Solid Films</u> , 302:155-161 (1997).
	AC	BASIT et al., "Crystallization of Pb(Zr, Ti)O ₃ films prepared by rf magnetron sputtering with a stoichiometric oxide target," <u>J. Vac. Sci. Technol.</u> , A 13(4):2214-2220 (1995).
	AD	BUHAY et al., "Pulsed laser deposition and ferroelectric characterization of bismuth titanate films," <u>Appl. Phys. Lett.</u> , 58(14):1470-1472 (1991).
	AE	DAX, M., eds., "The Non-Volatile Memory Challenge," <u>Semiconductor International</u> , September 1997, pages 84-92.
	AF	HAN et al., "SrBi ₂ Ta ₂ O ₉ memory capacitor on Si with a silicon nitride buffer," <u>Applied Physics Letters</u> , 72(10):1185-1186 (1998).
	AG	HIRAI et al., "Formation of Metal / Ferroelectric / Insulator / Semiconductor Structure with a CeO ₂ Buffer Layer," <u>Jpn. J. Appl. Phys.</u> , 33(9B)pt. 1: 5219-5222 (1994).
	AH	KIM et al., "Memory window of Pt-Bi ₂ Ta ₂ O ₉ /CeO ₂ /Si structure for metal ferroelectric insulator semiconductor field effect transistor," <u>Appl. Phys. Lett.</u> , 71(24):3507-3509 (1997).
	AI	MILLER et al., "Physics of the ferroelectric nonvolatile memory field effect transistor," <u>J. Appl. Phys.</u> , 72(12):5999-6010 (1992).
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	AK	ROST et al., "Ferroelectric switching of a field-effect transistor with a lithium niobate gate insulator," <u>Appl. Phys. Lett.</u> , 59(27):3654-3656 (1991).
	AL	SINHAROY et al., "Growth and characterization of ferroelectric BaMgF ₄ films," <u>J. Vac. Sci. Technol.</u> , A9(3):409-413 (1991).
	AM	TOKUMITSU et al., "Nonvolatile Memory Operations of Metal-Ferroelectric-Insulator-Semiconductor (MFIS) FET's Using PLZT/STO/Si(100) Structures," <u>IEEE Electric Device Letters</u> , 18(4):160-162 (1997).
	AN	WANG et al., "Deposition of in-plane textured MgO on amorphous Si ₃ N ₄ substrates ion-beam-assisted deposition and comparisons with ion-beam-assisted deposited yttria-stabilized-zirconia," <u>Appl. Phys. Lett.</u> , 71(20):2955-2957 (1997).
	AO	WU, Shu-Yau, "A New Ferroelectric Memory Device, Metal-Ferroelectric-Semiconductor Transistor," <u>IEEE Transactions on Electron Devices</u> , ED-21(8):499-504 (1974).

Examiner Signature

Date Considered

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